L Number	Hits	Search Text	DB	Time stamp
-	119	257/625.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/13 12:38
-	113	257/625.ccls. and (@ad<20010501)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/13 12:48
-	191	438/740.ccls. and (@ad<20010501)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/13 12:49
-	115	(438/740.ccls. and (@ad<20010501)) and wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/13 12:52
-	59	257/459.ccls. and (tan or wn or tasn or sin or tungsten or tantalum or (etch adj stop))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/13 13:17
-	174	438/459.ccls. and (tan or wn or tasn or sin or tungsten or tantalum or (etch adj stop))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/13 14:02
-	3135	(wafer or (semiconductor adj substrate)) near (trench or cavity or recess)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/13 14:01
-	5503	(wafer or (semiconductor adj substrate)) near (via or trench or cavity or recess)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/13 14:01
-	5	(plastic adj mold) near epoxy	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/13 14:16
-	36	((wafer or (semiconductor adj substrate)) near (via or trench or cavity or recess)) and ((trench or cavity or recess or via) near (tan or wn or tasn or sin or tungsten or tantalum or (etch adj stop)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/13 14:22